

# **isc Silicon NPN Darlington Power Transistor**

### **DESCRIPTION**

- · High DC Current Gain
  - : h<sub>FE</sub>= 2000(Min.)@ I<sub>C</sub>= 5A, V<sub>CE</sub>= 2V
- · Collector-Emitter Breakdown Voltage-
  - :  $V_{(BR)CEO} = 60V(Min.)$
- Complement to Type 2SB912
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

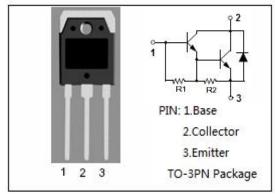


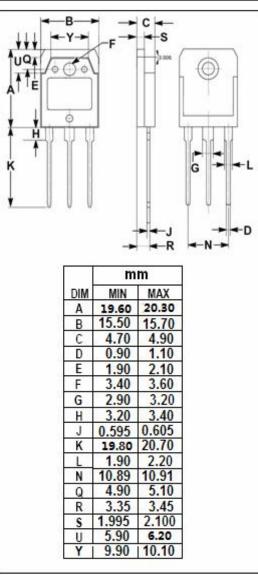
## **APPLICATIONS**

• Designed for motor drivers, printer hammer drivers, relay drivers, voltage regulator control applications.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	70	V	
Vceo	Collector-Emitter Voltage	60	٧	
V <sub>EBO</sub>	Emitter-Base Voltage	6	٧	
lc	Collector Current-Continuous	10	Α	
I <sub>CM</sub>	Collector Current-Peak	15	Α	
P <sub>C</sub>	Collector Power Dissipation @T <sub>a</sub> =25°C	2.5	W	
	Collector Power Dissipation @T <sub>C</sub> =25°C	60	VV	
T <sub>j</sub>	Junction Temperature	150	$^{\circ}\mathbb{C}$	
T <sub>stg</sub>	Storage Temperature Range	Range -55~150		







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2SD1229

### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT		
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 30mA; R <sub>BE</sub> = ∞	60			V		
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA; I <sub>E</sub> = 0	70			V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A, I <sub>B</sub> = 10mA			1.5	V		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A, I <sub>B</sub> = 10mA			2.0	V		
I <sub>CBO</sub>	Collector Cutoff current	V <sub>CB</sub> = 40V, I <sub>E</sub> = 0			0.1	mA		
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			3.0	mA		
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 5A; V <sub>CE</sub> = 5V		20		MHz		
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 5A; V <sub>CE</sub> = 2V	2000					
Switching Times								
t <sub>on</sub>	Turn-On Time			0.6		μS		
t <sub>stg</sub>	Storage Time	$I_C = 5A$ , $I_{B1} = I_{B2} = 10mA$ ; $R_L = 4 \Omega$ ; $V_{CC} = 20V$		3.0		μS		
t <sub>f</sub>	Fall Time			1.8		μS		

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